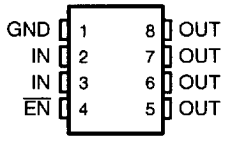
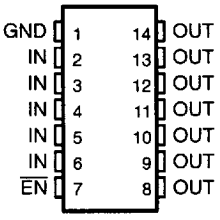
- 95-mΩ Max (5.5-V Input) High-Side MOSFET Switch With Logic Compatible Enable Input
- Short-Circuit and Thermal Protection
- Typical Short-Circuit Current Limits: 0.4 A, TPS2010; 1.2 A, TPS2011; 2 A, TPS2012; 2.6 A, TPS2013
- Electrostatic-Discharge Protection, 12-kV Output, 6-kV All Other Terminals
- Controlled Rise and Fall Times to Limit Current Surges and Minimize EMI
- SOIC-8 Package Pin Compatible With the Popular Littlefoot™ Series When GND Is Connected
- 2.7-V to 5.5-V Operating Range
- 10-μA Maximum Standby Current
- Surface-Mount SOIC-8 and TSSOP-14 Packages
- –40°C to 125°C Operating Junction Temperature Range

D PACKAGE
(TOP VIEW)



PW PACKAGE
(TOP VIEW)



description

The TPS201x family of power-distribution switches is intended for applications where heavy capacitive loads and short circuits are likely to be encountered. The high-side switch is a 95-mΩ N-channel MOSFET. Gate drive is provided by an internal driver and charge pump designed to control the power switch rise times and fall times to minimize current surges during switching. The charge pump operates at 100 kHz, requires no external components, and allows operation from supplies as low as 2.7 V. When the output load exceeds the current-limit threshold or a short circuit is present, the TPS201x limits the output current to a safe level by switching into a constant-current mode. Continuous heavy overloads and short circuits increase power dissipation in the switch and cause the junction temperature to rise. If the junction temperature reaches approximately 180°C, a thermal protection circuit shuts the switch off to prevent damage. Recovery from thermal shutdown is automatic once the device has cooled sufficiently.

The members of the TPS201x family differ only in short-circuit current threshold. The TPS2010 is designed to limit at 0.4-A load; the other members of the family limit at 1.2 A, 2 A, and 2.6 A (see the available options table). The TPS201x family is available in SOIC-8 and TSSOP-14 packages and operates over a junction temperature range of –40°C to 125°C. Versions in the SOIC-8 package are drop-in replacements for Siliconix's Littlefoot™ power PMOS switches, except that GND must be connected.

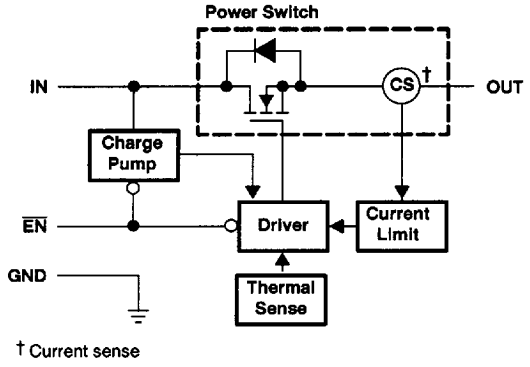
AVAILABLE OPTIONS

T_J	RECOMMENDED MAXIMUM CONTINUOUS LOAD CURRENT (A)	TYPICAL SHORT-CIRCUIT OUTPUT CURRENT LIMIT AT 25°C (A)	PACKAGE	
			SOIC (D)†	TSSOP (PW)‡
–40°C to 125°C	0.2	0.4	TPS2010D	TPS2010PWLE
	0.6	1.2	TPS2011D	TPS2011PWLE
	1	2	TPS2012D	TPS2012PWLE
	1.5	2.6	TPS2013D	TPS2013PWLE

† The D package is available taped and reeled. Add an R suffix to device type (e.g., TPS2010DR).
‡ The PW package is only available left-end taped and reeled (indicated by the LE suffix on the device type; e.g., TPS2010PWLE).

Littlefoot is a trademark of Siliconix.

functional block diagram



Terminal Functions

TERMINAL			I/O	DESCRIPTION
NAME	NO.			
	D	PW		
$\overline{EN}$	4	7	I	Enable input. Logic low turns power switch on.
GND	1	1	I	Ground
IN	2, 3	2–6	I	Input voltage
OUT	5–8	8–14	O	Power-switch output

detailed description

power switch

The power switch is an N-channel MOSFET with a maximum on-state resistance of 95 mΩ ($V_{I(IN)}$ = 5.5 V), configured as a high-side switch.

charge pump

An internal 100-kHz charge pump supplies power to the driver circuit and provides the necessary voltage to pull the gate of the MOSFET above the source. The charge pump operates from input voltages as low as 2.7 V and requires very little supply current.

driver

The driver controls the gate voltage of the power switch. To limit large current surges and reduce the associated electromagnetic interference (EMI) produced, the driver incorporates circuitry that controls the rise times and fall times of the output voltage. The rise and fall times are typically in the 2-ms to 4-ms range instead of the microsecond or nanosecond range for a standard FET.

enable ($\overline{EN}$)

A logic high on the $\overline{EN}$ input turns off the power switch and the bias for the charge pump, driver, and other circuitry to reduce the supply current to less than 10 μA. A logic zero input restores bias to the drive and control circuits and turns the power on. The enable input is compatible with both TTL and CMOS logic levels.

current sense

A sense FET is used to monitor the current supplied to the load. The sense FET is a much more efficient way to measure current than conventional resistance methods. When an overload or short circuit is encountered, the current-sense circuitry sends a control signal to the driver. The driver in turn reduces the gate voltage and drives the power FET into its linear region, which switches the output into a constant current mode and simply holds the current constant while varying the voltage on the load.

thermal sense

An internal thermal-sense circuit is used to shut the power switch off if the junction temperature rises to approximately 180°C. Hysteresis is built into the thermal sense, and after the device has cooled approximately 20 degrees, the switch turns back on. The switch continues to cycle off and on until the fault is removed.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Input voltage range, $V_{I(IN)}$ (see Note 1) ..... −0.3 V to 7 V
Output voltage range, V_O (see Note 1) ..... −0.3 V to $V_{I(IN)}$ +0.3 V
Input voltage range, V_I at $\overline{EN}$ ..... −0.3 V to 7 V
Continuous output current, I_O ..... internally limited
Continuous total power dissipation ..... See Dissipation Rating Table
Operating virtual junction temperature range, T_J ..... −40°C to 125°C
Storage temperature range ..... −65°C to 150°C
Lead temperature soldering 1,6 mm (1/16 inch) from case for 10 seconds ..... 260°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltages are with respect to GND.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25°C$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25°C$	$T_A = 70°C$ POWER RATING	$T_A = 125°C$ POWER RATING
D	725 mW	5.8 mW/°C	464 mW	145 mW
PW	700 mW	5.6 mW/°C	448 mW	140 mW

recommended operating conditions

		MIN	MAX	UNIT
Input voltage, $V_{I(IN)}$		2.7	5.5	V
Input voltage, V_I at $\overline{EN}$		0	5.5	V
Continuous output current, I_O	TPS2010	0	0.2	A
	TPS2011	0	0.6	
	TPS2012	0	1	
	TPS2013	0	1.5	
Operating virtual junction temperature, T_J		−40	125	°C

electrical characteristics over recommended operating junction temperature range, $V_{I(IN)}$ = 5.5 V, I_O = rated current, $\overline{EN}$ = 0 V (unless otherwise noted)

power switch

PARAMETER	TEST CONDITIONS†		MIN	TYP	MAX	UNIT
On-state resistance	$V_{I(IN)}$ = 5.5 V,	T_J = 25°C		75	95	mΩ
	$V_{I(IN)}$ = 4.5 V,	T_J = 25°C		80	110	
	$V_{I(IN)}$ = 3 V,	T_J = 25°C		120	175	
	$V_{I(IN)}$ = 2.7 V,	T_J = 25°C		140	215	
Output leakage current	$\overline{EN}$ = $V_{I(IN)}$	T_J = 25°C		0.001	1	µA
		−40°C ≤ T_J ≤ 125°C			10	
Output rise time	$V_{I(IN)}$ = 5.5 V,	T_J = 25°C, C_L = 1 µF		4		ms
	$V_{I(IN)}$ = 2.7 V,	T_J = 25°C, C_L = 1 µF		3.8		
Output fall time	$V_{I(IN)}$ = 5.5 V,	T_J = 25°C, C_L = 1 µF		3.9		ms
	$V_{I(IN)}$ = 2.7 V,	T_J = 25°C, C_L = 1 µF		3.5		

† Pulse-testing techniques are used to maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

enable input ($\overline{EN}$)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
High-level input voltage	2.7 V ≤ $V_{I(IN)}$ ≤ 5.5 V	2			V
Low-level input voltage	4.5 V ≤ $V_{I(IN)}$ ≤ 5.5 V			0.8	V
	2.7 V ≤ $V_{I(IN)}$ < 4.5 V			0.4	
Input current	$\overline{EN}$ = 0 V or $\overline{EN}$ = $V_{I(IN)}$	−0.5		0.5	µA
Propagation (delay) time, low-to-high-level output	C_L = 1 µF			20	ms
Propagation (delay) time, high-to-low-level output	C_L = 1 µF			40	

current limit

PARAMETER	TEST CONDITIONS†		MIN	TYP	MAX	UNIT
Short-circuit current	T_J = 25°C, $V_{I(IN)}$ = 5.5 V, OUT connected to GND, device enabled into short circuit	TPS2010	0.22	0.4	0.6	A
		TPS2011	0.66	1.2	1.8	
		TPS2012	1.1	2	3	
		TPS2013	1.65	2.6	4.5	

† Pulse-testing techniques are used to maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

supply current

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Supply current, low-level output	$\overline{EN}$ = $V_{I(IN)}$	T_J = 25°C		0.015	1	µA
		−40°C ≤ T_J ≤ 125°C			10	
Supply current, high-level output	$\overline{EN}$ = 0 V	T_J = 25°C		73	100	µA
		−40°C ≤ T_J ≤ 125°C			100	

PARAMETER MEASUREMENT INFORMATION

timing diagrams

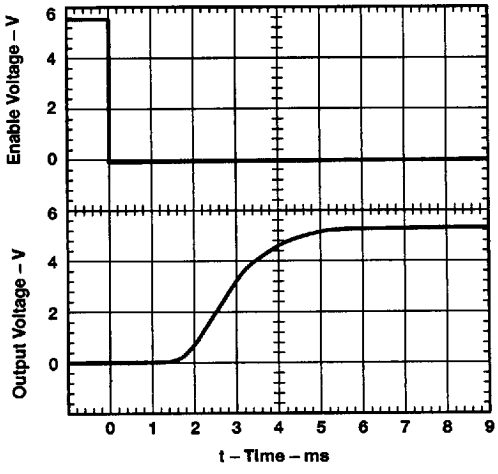


Figure 1. Propagation Delay and Rise Time With 1-μF Load, $V_{I(IN)}$ = 5.5 V

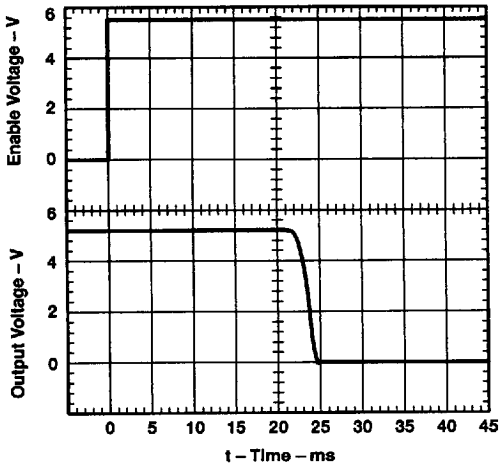


Figure 2. Propagation Delay and Fall Time With 1-μF Load, $V_{I(IN)}$ = 5.5 V

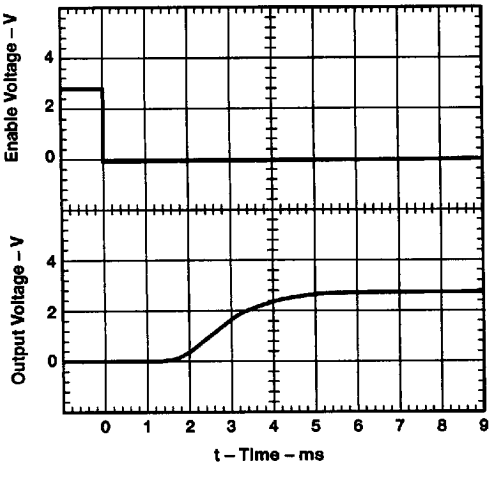


Figure 3. Propagation Delay and Rise Time With 1-μF Load, $V_{I(IN)}$ = 2.7 V

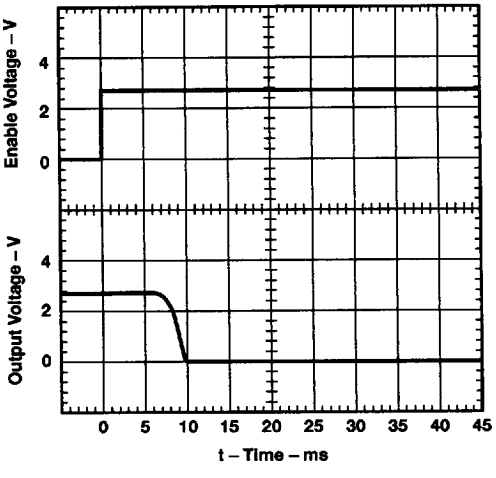


Figure 4. Propagation Delay and Fall Time With 1-μF Load, $V_{I(IN)}$ = 2.7 V

PARAMETER MEASUREMENT INFORMATION

timing diagrams (continued)

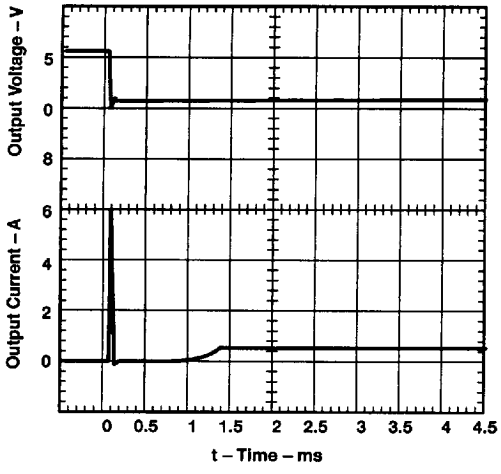


Figure 5. TPS2010, Short-Circuit Current. Short Is Applied to Enabled Device, $V_{I(IN)}$ = 5.5 V

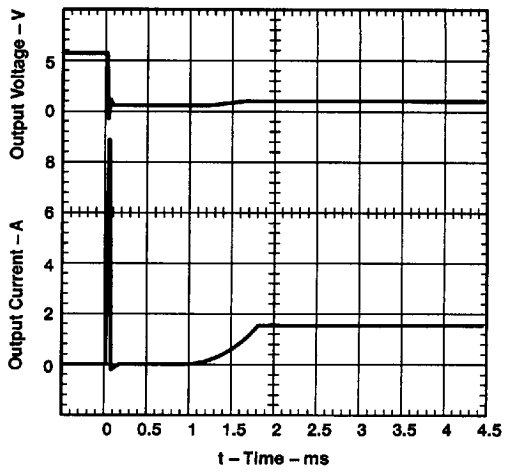


Figure 6. TPS2011, Short-Circuit Current. Short Is Applied to Enabled Device, $V_{I(IN)}$ = 5.5 V

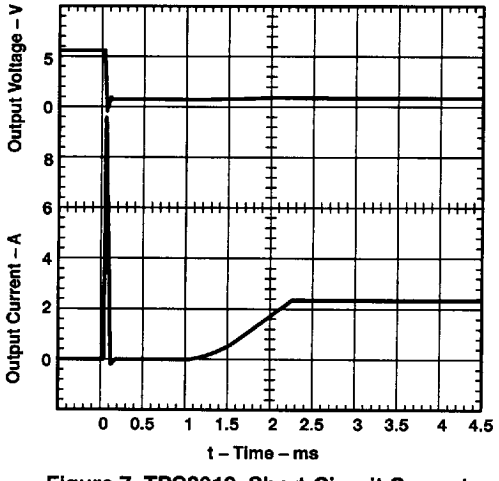


Figure 7. TPS2012, Short-Circuit Current. Short is Applied to Enabled Device, $V_{I(IN)}$ = 5.5 V

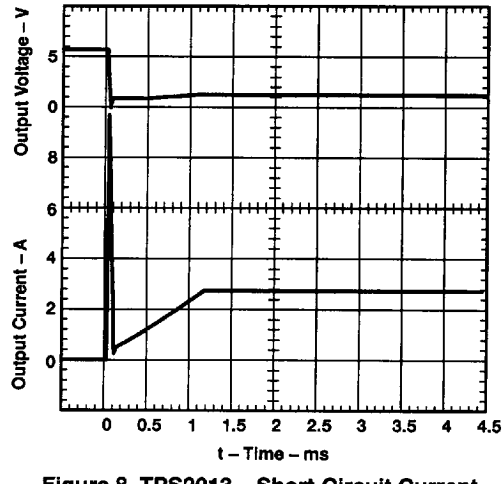


Figure 8. TPS2013 – Short-Circuit Current. Short is Applied to Enabled Device, $V_{I(IN)}$ = 5.5 V

PARAMETER MEASUREMENT INFORMATION

timing diagrams (continued)

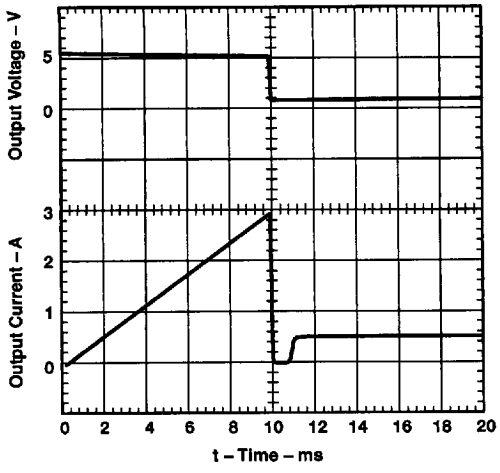


Figure 9. TPS2010 – Threshold Current, $V_{I(IN)}$ = 5.5 V

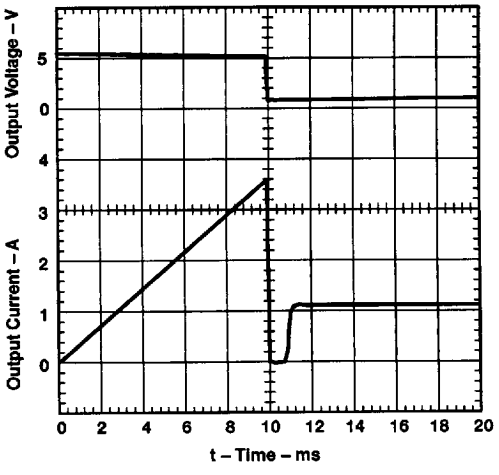


Figure 10. TPS2011 – Threshold Current, $V_{I(IN)}$ = 5.5 V

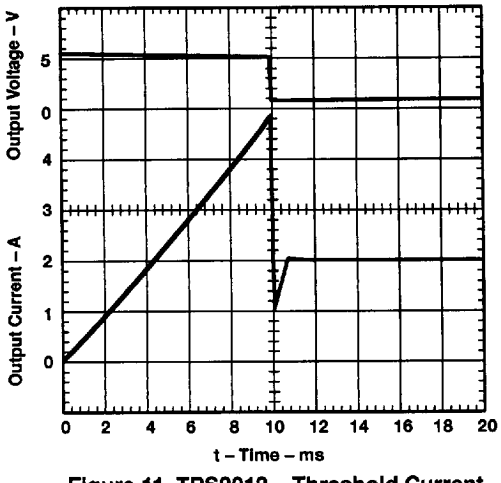


Figure 11. TPS2012 – Threshold Current, $V_{I(IN)}$ = 5.5 V

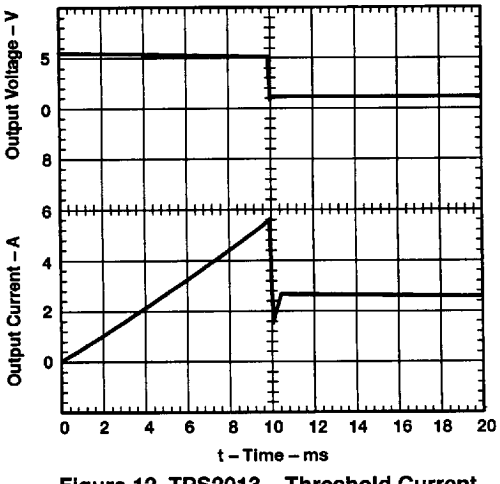


Figure 12. TPS2013 – Threshold Current, $V_{I(IN)}$ = 5.5 V

PARAMETER MEASUREMENT INFORMATION

timing diagrams (continued)

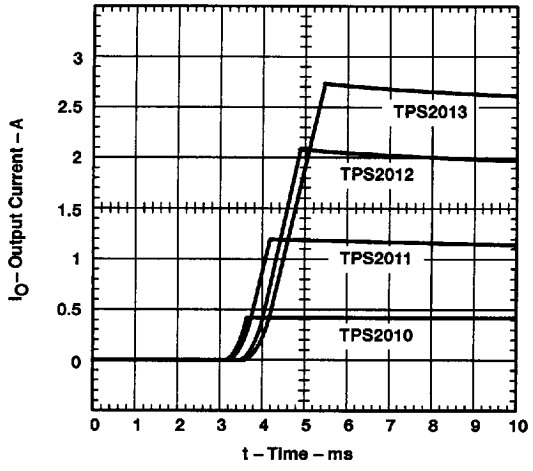


Figure 13. Turned-On (Enabled) Into Short Circuit, $V_{I(IN)}$ = 5.5 V

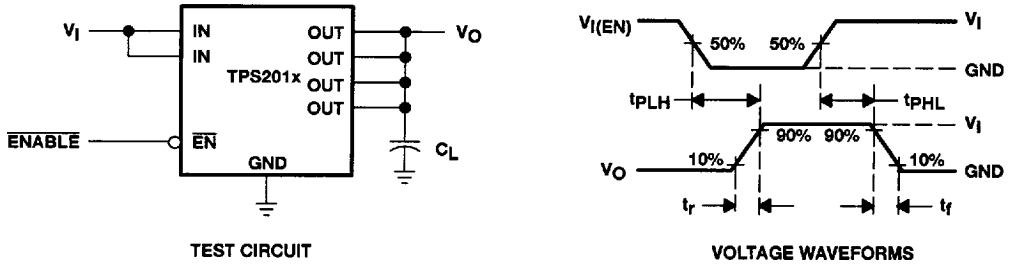


Figure 14. Test Circuit and Voltage Waveforms

TYPICAL CHARACTERISTICS

TURN-ON DELAY vs INPUT VOLTAGE

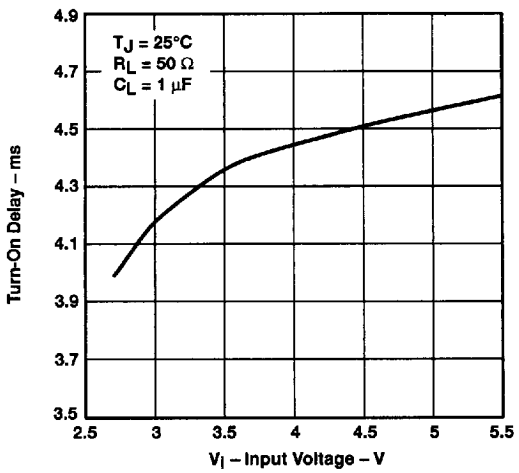


Figure 15

TURN-OFF DELAY vs INPUT VOLTAGE

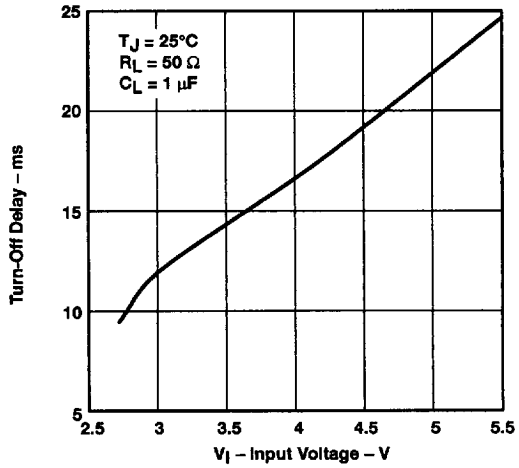


Figure 16

RISE TIME vs OUTPUT CURRENT

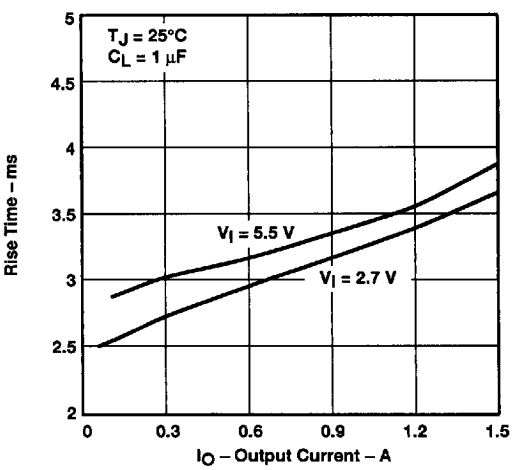


Figure 17

FALL TIME vs OUTPUT CURRENT

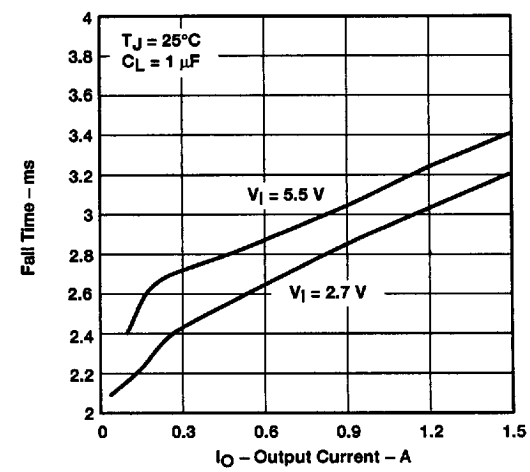


Figure 18

TYPICAL CHARACTERISTICS

SUPPLY CURRENT, OUTPUT ENABLED
vs
JUNCTION TEMPERATURE

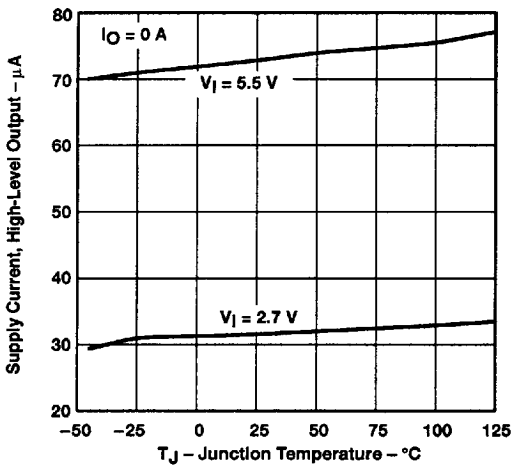


Figure 19

SUPPLY CURRENT, OUTPUT DISABLED
vs
JUNCTION TEMPERATURE

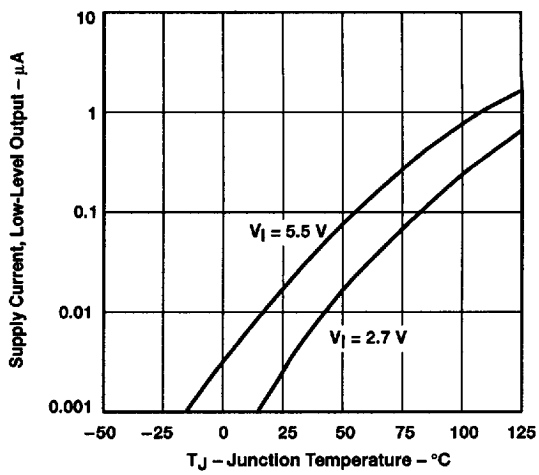


Figure 20

SUPPLY CURRENT, OUTPUT ENABLED
vs
INPUT VOLTAGE

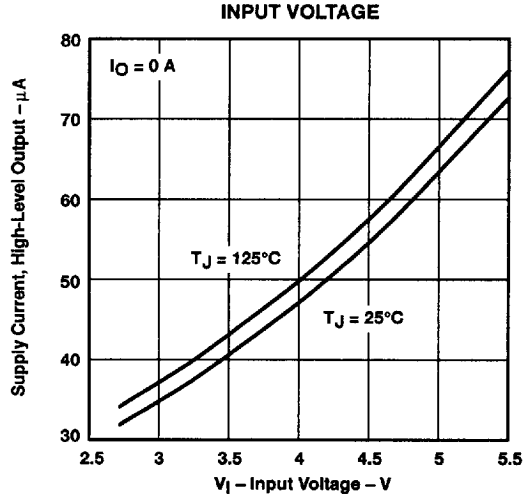


Figure 21

SUPPLY CURRENT, OUTPUT DISABLED
vs
INPUT VOLTAGE

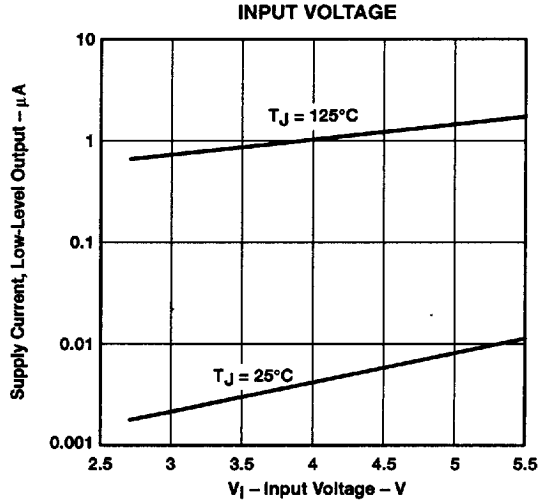


Figure 22

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TYPICAL CHARACTERISTICS

ON-STATE RESISTANCE
vs
JUNCTION TEMPERATURE

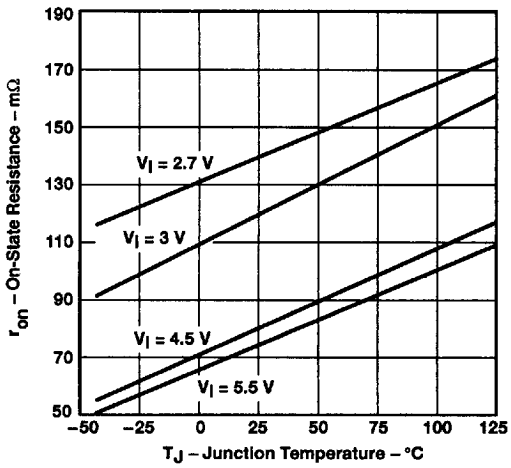

Figure 23

ON-STATE RESISTANCE
vs
INPUT VOLTAGE

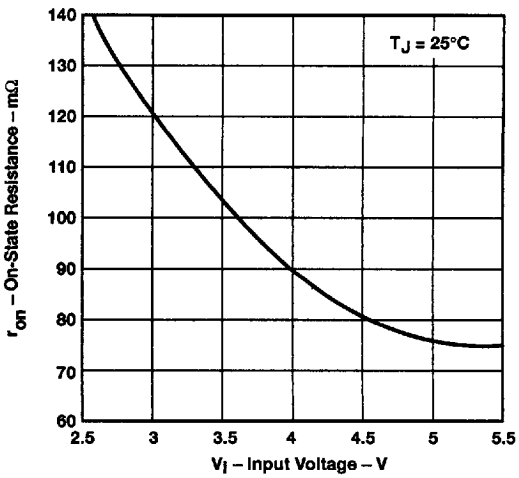

Figure 24

INPUT VOLTAGE TO OUTPUT VOLTAGE
vs
INPUT VOLTAGE

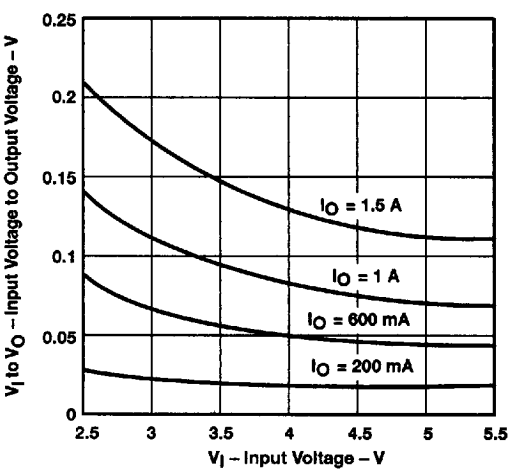

Figure 25

SHORT-CIRCUIT CURRENT
vs
INPUT VOLTAGE

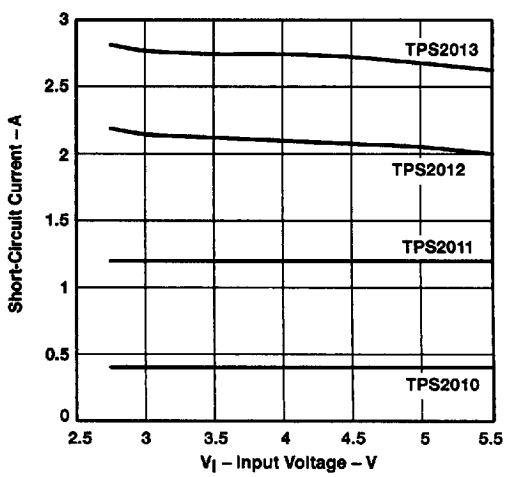

Figure 26

TYPICAL CHARACTERISTICS

THRESHOLD TRIP CURRENT
vs
INPUT VOLTAGE

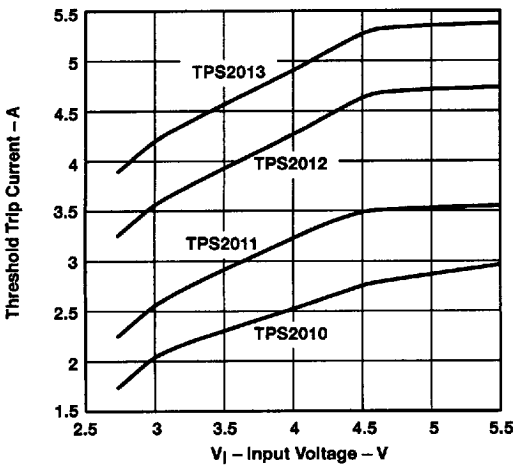

Figure 27

SHORT-CIRCUIT CURRENT
vs
JUNCTION TEMPERATURE

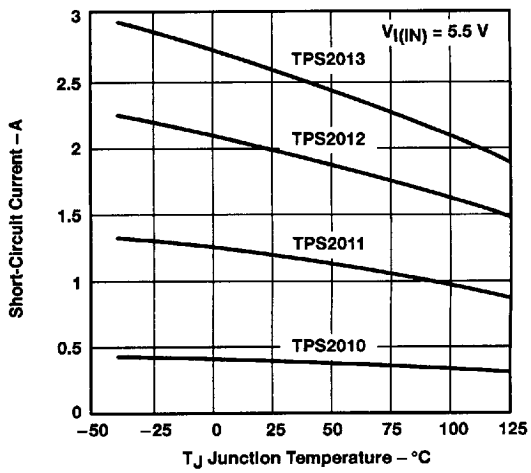

Figure 28

APPLICATION INFORMATION

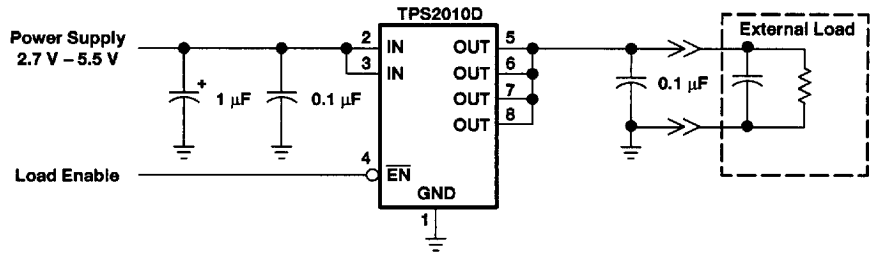

Figure 29. Typical Application

power supply considerations

The TPS201x family has multiple inputs and outputs, which must be connected in parallel to minimize voltage drop and prevent unnecessary power dissipation.

A 0.047-µF to 0.1-µF ceramic bypass capacitor between IN and GND, close to the device, is recommended. A high-value electrolytic capacitor is also desirable when the output load is heavy or has large paralleled capacitors. Bypassing the output with a 0.1-µF ceramic capacitor improves the immunity of the device to electrostatic discharge (ESD).

overcurrent

A sense FET is employed to check for overcurrent conditions. Unlike sense resistors and polyfuses, sense FETs do not increase series resistance to the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduce the output voltage accordingly. Shutdown only occurs if the fault is present long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted before the device is enabled or before $V_{I(IN)}$ has been applied (see Figure 30). The TPS201x senses the short and immediately switches into a constant-current output.

Under the second condition, the short occurs while the device is enabled. At the instant the short occurs, very high currents flow for a short time before the current-limit circuit can react (see Figures 5, 6, 7, and 8). After the current-limit circuit has tripped, the device limits normally.

Under the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold is reached (see Figures 9, 10, 11, and 12). The TPS201x family is capable of delivering currents up to the current-limit threshold without damage. Once the threshold has been reached, the device switches into its constant-current mode.

APPLICATION INFORMATION

overcurrent (continued)

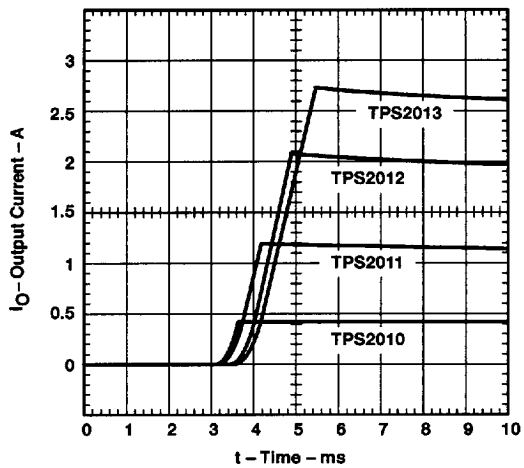

Figure 30. Turned-On (Enabled) Into Short Circuit, $V_{I(IN)}$ = 5.5 V

power dissipation and junction temperature

The low on resistance of the N-channel MOSFET allows small surface-mount packages, such as SOIC or TSSOP to pass large currents. The thermal resistances of these packages is high compared to that of power packages; it is good design practice to check power dissipation and junction temperature. The first step is to find r_{on} at the input voltage and operating temperature. As an initial estimate, use the highest operating ambient temperature of interest and and read r_{on} from Figure 23. Next calculate the power dissipation using:

$$P_D = r_{on} \times I^2$$

Finally, calculate the junction temperature:

$$T_J = P_D \times R_{\theta JA} + T_A$$

Where:

T_A = Ambient temperature
$R_{\theta JA}$ = Thermal resistance SOIC = 172°C/W, TSSOP = 179°C/W

Compare the calculated junction temperature with the initial estimate. If they do not agree within a few degrees, repeat the calculation using the calculated value as the new estimate. Two or three iterations is generally sufficient to get a reasonable answer.

APPLICATION INFORMATION

thermal protection

Thermal protection is provided to prevent damage to the IC when heavy-overload or short-circuit faults are present for extended periods of time. The faults force the TPS201x into its constant current mode, which causes the voltage across the high-side switch to increase; under short-circuit conditions, the voltage across the switch is equal to the input voltage. The increased dissipation causes the junction temperature to rise to dangerously high levels. The protection circuit senses the junction temperature of the switch and shuts it off. The switch remains off until the junction has dropped approximately 20°C. The switch continues to cycle in this manner until the load fault or input power is removed.

ESD protection

All TPS201x terminals incorporate ESD-protection circuitry designed to withstand a 6-kV human-body-model discharge as defined in MIL-STD-883C. Additionally, the output is protected from discharges up to 12 kV.